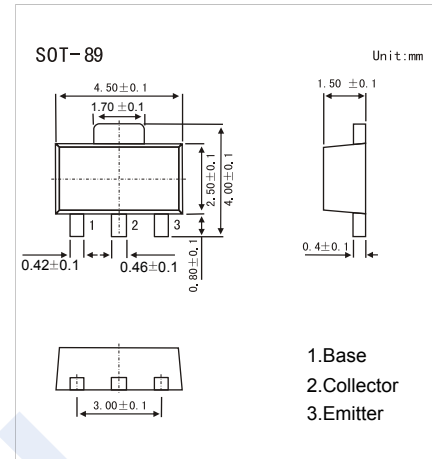


NPN Transistors

2SD1368

■ Features

- Low frequency power amplifier
- Complementary to 2SB1002



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	100	V
Collector - Emitter Voltage	V _{CE0}	50	
Emitter - Base Voltage	V _{EB0}	6	
Collector Current - Continuous	I _C	1	A
Collector Current - Pulse (Note.1)	I _{CP}	1.5	
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

Note.1:PW ≤ 10 ms, Duty cycle ≤ 20%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C = 100 uA, I _E = 0	100			V
Collector-emitter breakdown voltage	V _{CE0}	I _C = 1 mA, R _{BE} = ∞	50			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 uA, I _C = 0	6			
Collector-base cut-off current	I _{CB0}	V _{CB} = 80 V, I _E = 0			0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _C =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1 A, I _B =100mA			0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =1 A, I _B =100mA			1.2	
DC current gain	h _{FE}	V _{CE} = 2V, I _C = 0.1 A	100		500	
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz		20		pF
Transition frequency	f _t	V _{CE} = 2V, I _C = 10mA		100		MHz

■ Classification of h_{FE}

Type	2SD1368-A	2SD1368-B	2SD1368-C
Range	100-200	160-320	250-500
Marking	CA	CB	CC

NPN Transistors

2SD1368

■ Typical Characteristics

